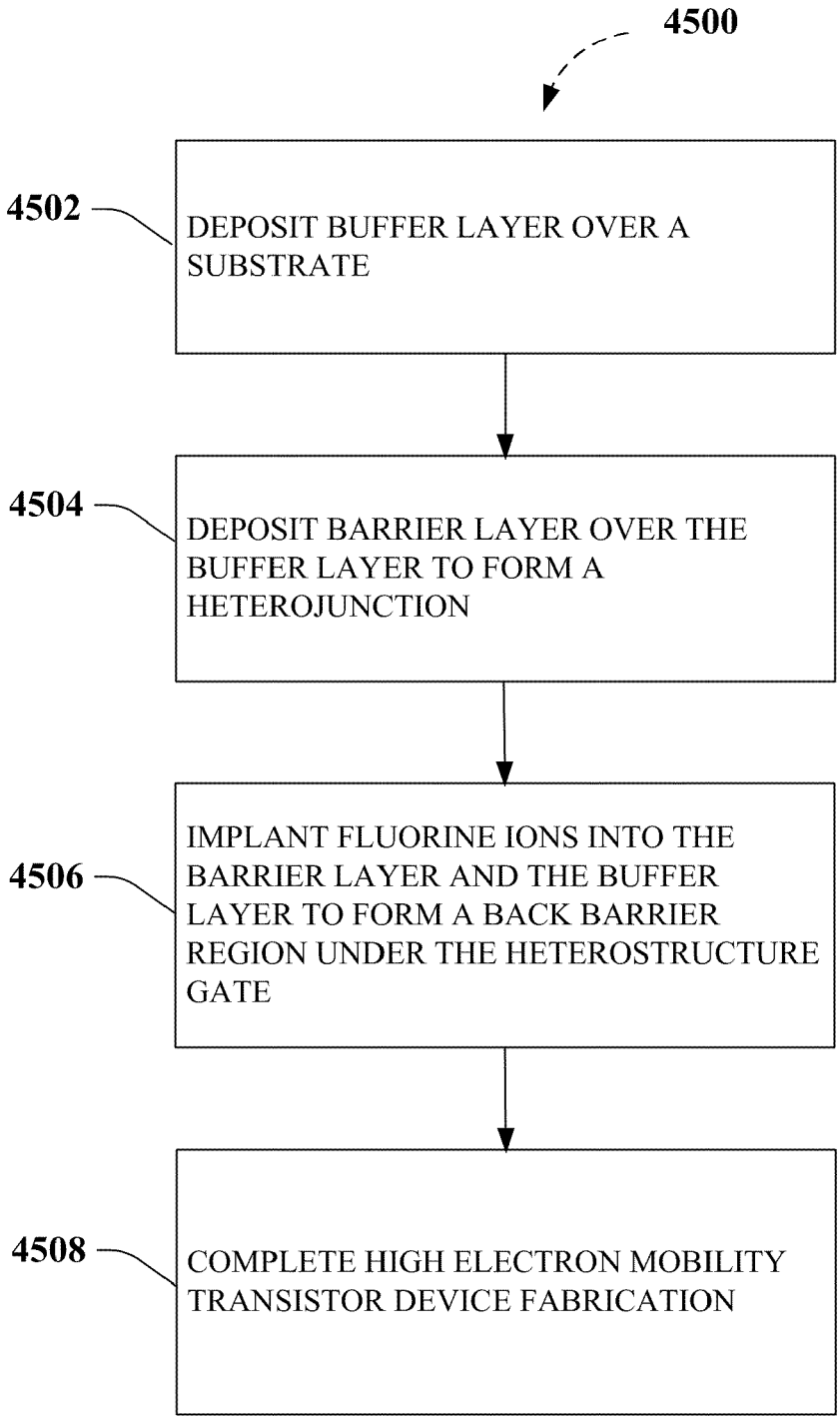
4500
4502
DEPOSIT BUFFER LAYER OVER A SUBSTRATE
4504
DEPOSIT BARRIER LAYER OVER THE BUFFER LAYER TO FORM A HETEROJUNCTION
4506
IMPLANT FLUORINE IONS INTO THE BARRIER LAYER AND THE BUFFER LAYER TO FORM A BACK BARRIER REGION UNDER THE HETEROSTRUCTURE GATE
4508
COMPLETE HIGH ELECTRON MOBILITY TRANSISTOR DEVICE FABRICATION

FIG. 45